

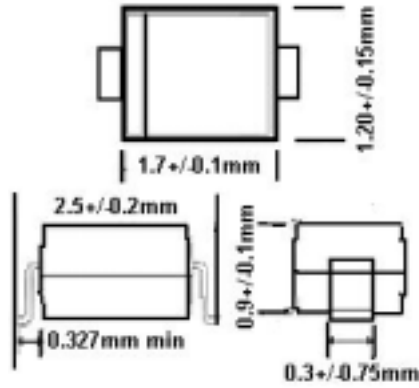


**200mW SURFACE MOUNT
ZENER DIODE**

Description

Mechanical Dimensions

BZT52C2V4S~39S



SOD-323

DIMENSIONS IN MM

Features:

Power dissipation: Pd: 200mW (tamb=25C)

Forward Voltage: Vf: 0.9V

Operating and storage junction temp. range: Tj, Tstg: -55C to +150C

Maximum ratings (Tamb=25C unless otherwise specified)

Characteristic	Symbol	Value	Unite
Forward Voltage (note 2) @If=10mA	Vf	0.9	V
Power issipation (note 1)	Pd	200	mW
Thermal Resistance Junction to Ambie	RjA	625	C/W
Operating and Storage Temp. Range	Tj, Tstg	-65~+150	C

Note 1: Vald provided that device terminals are kept at ambient temp.

Note 2: Shart duration test pulse used in minimize self-hearing effect.

Note 3: f=1KHZ



200 mW FCI Part #	Nominal Zener Voltage @ Izt Vz (V)	Test Current Izt (mA)	Maximum Zener ImpedanceVzt @ Izt;Vzk@ Izk=0.5mA Vzt / Vzk(ohm)	Maximum Reverse Current Ir(uA) @ Vr(V)	Forward Voltage VF (V) IF (mA)	Marking	Package
BZT52C2V4S	2.4	5	100/1000	50 / 1.0	0.9 / 10	00	SOD-323
BZT52C2V7S	2.7	5	100/1000	20/1.0	0.9 / 10	01	
BZT52C3V0S	3.0	5	100/1000	10/1.0	0.9 / 10	02	
BZT52C3V3S	3.3	5	95/1000	5/1.0	0.9 / 10	05	
BZT52C3V6S	3.6	5	90/1000	5/1.0	0.9 / 10	06	
BZT52C3V9S	3.9	5	90/1000	3/1.0	0.9 / 10	07	
BZT52C4V3S	4.3	5	90/1000	3/1.0	0.9 / 10	08	
BZT52C4V7S	4.7	5	80/800	3/2.0	0.9 / 10	09	
BZT52C5V1S	5.1	5	60/500	2/2.0	0.9 / 10	0A	
BZT52C5V6S	5.6	5	40/200	1/2.0	0.9 / 10	0C	
BZT52C6V2S	6.2	5	10/100	3/4.0	0.9 / 10	0E	
BZT52C6V8S	6.8	5	15/160	2/4.0	0.9 / 10	0F	
BZT52C7V5S	7.5	5	15/160	1/5.0	0.9 / 10	0G	
BZT52C8V2S	8.2	5	15/160	0.70/5.0	0.9 / 10	0H	
BZT52C9V1S	9.1	5	15/160	0.20/7.0	0.9 / 10	0K	
BZT52C10S	10	5	20/160	0.10/8.0	0.9 / 10	0L	
BZT52C11S	11	5	20/160	0.10/8.0	0.9 / 10	0M	
BZT52C12S	12	5	25/80	0.10/8.0	0.9 / 10	0N	
BZT52C13S	13.25	5	30/80	0.10/8.0	0.9 / 10	0P	
BZT52C15S	15	5	30/80	0.05/10.5	0.9 / 10	0T	
BZT52C16S	16.2	5	40/80	0.05/11.2	0.9 / 10	0U	
BZT52C18S	18	5	45/80	0.05/12.6	0.9 / 10	0W	
BZT52C20S	20	5	55/100	0.05/14.0	0.9 / 10	0Z	
BZT52C22S	22	5	55/100	0.05/15.4	0.9 / 10	10	
BZT52C24S	24.2	5	70/120	0.05/16.8	0.9 / 10	11	
BZT52C27S	27	5	80/300	0.05/18.9	0.9 / 10	12	
BZT52C30S	30	5	80/300	0.05/21.0	0.9 / 10	14	
BZT52C33S	33	5	80/300	0.05/23.2	0.9 / 10	18	
BZT52C36S	36	5	90/350	0.05/25.2	0.9 / 10	19	
BZT52C39S	39	5	130/350	0.05/27.3	0.9 / 10	20	

Device tolerance 8%

TYPICAL CHARACTERISTICS

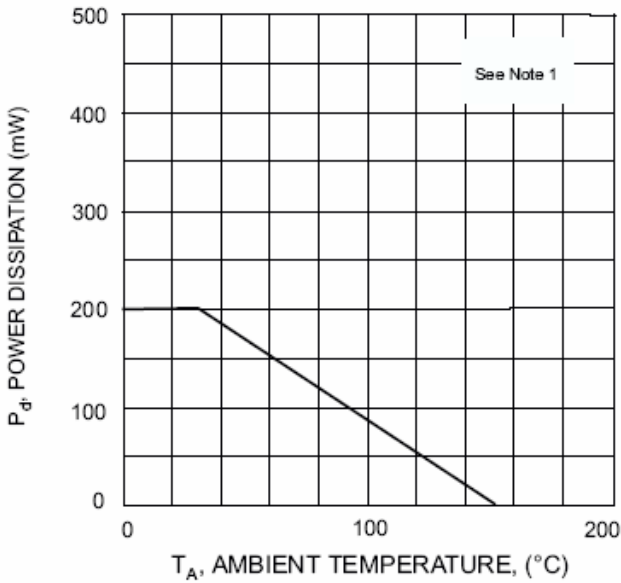


Fig. 1 Power Derating Curve

BZT52C2V4S-BZT52C39S

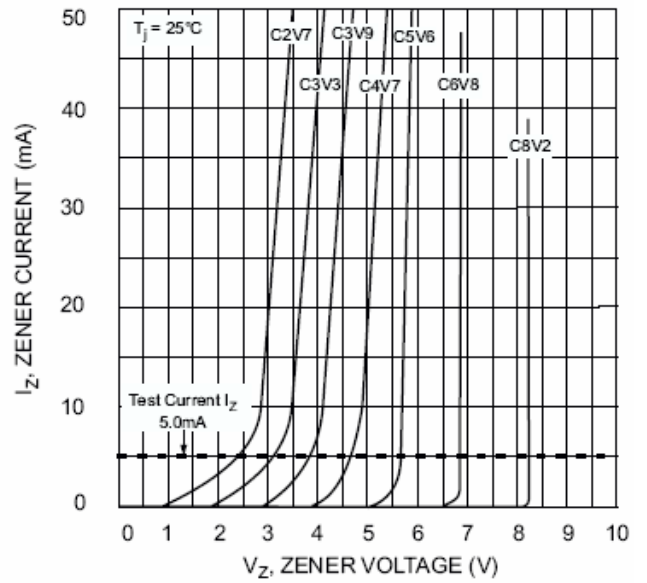


Fig. 2 Zener Breakdown Characteristics

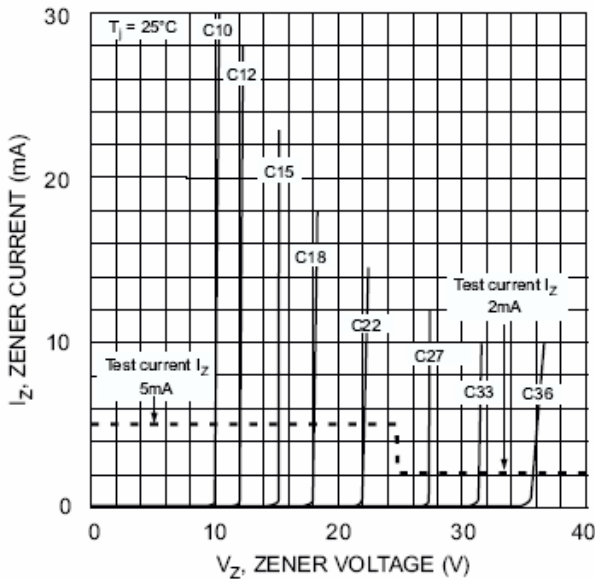


Fig. 3 Zener Breakdown Characteristics

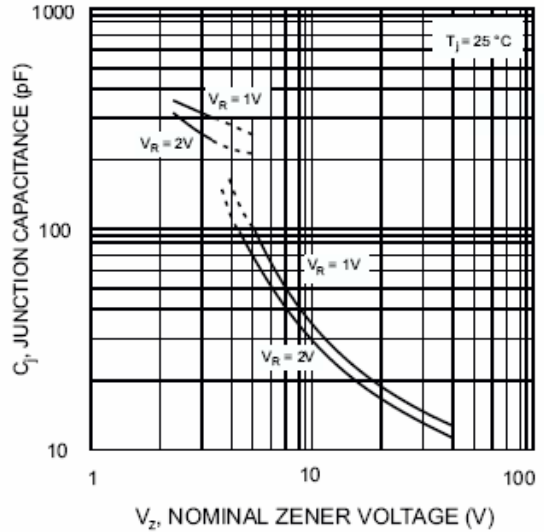


Fig. 4 Junction Capacitance vs. Nominal Zener Voltage